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## **Report:**

The GeTe-CuTe system (GCT) has been proposed as a new phase change material (PCM) class, and it is expected to be used for a next generation of data storage (non-volatile) memories instead of the usual Ge-Sb-Te (GST) alloys. In particular, the composition  $Ge_1Cu_1Te_2$  is of special interest for electronic memories, as it possesses a considerable electrical contrast between the amorphous and the crystalline phase while offering a negligible change in the macroscopic density [1], thereby greatly enhancing the life-time and cyclability of the data carrier. To elucidate the structure-property relations in this amorphous compound, we conducted anomalous X-ray scattering (AXS) experiments close to the *K*-edges of all the constituent elements. In combination with the use of reverse Monte Carlo modelling, we are able to characterize the short- and intermediate-range atomic structures (SRO and IRO, respectively).

GCT crystalline films were found to be easily amorphised by laser irradiation with a lower power and short pulse width [2], which are essential properties to achieve rapid data recording and low power consumption in a PCM. In contrast to widely studied PCMs like GST, amorphous Ge-Cu-Te compounds exhibit a complex compositional dependence of the phase-change properties like the density change or the optical contrast  $\Delta R_{opt}$ . In the case of Ge<sub>1</sub>Cu<sub>1</sub>Te<sub>2</sub>, these two properties are close to zero, while taking negative values for higher contents of Cu. On the other hand, a considerable electrical contrast between the amorphous and crystalline phase remains even in Ge<sub>1</sub>Cu<sub>1</sub>Te<sub>2</sub>, rendering it suitable for PCM applications. Despite its significance among the GCT PCMs, the composition Ge<sub>1</sub>Cu<sub>1</sub>Te<sub>2</sub> proposed for the experiment herein has not yet been subject to experimental or theoretical investigations. However, it may represent the cornerstone to develop a new concept to understand the optical contrast in PCMs. This property has been described for the Ge-Sb-Te system and was understood to arise from a large difference in the optical matrix elements [3], i.e. these are enhanced in the crystal by aligned rows of resonantly bonded *p*-orbitals, while the amorphous phase has no enhancement due to an absence of this order. This model alone however cannot explain the complex dependence of  $\Delta R_{opt}$  in GCT, so that a new concept is necessary to understand the structure-property relations.

The experiment results indicate that no sudden jump in the structure of the amorphous phase occurs along the pseudo-binary line GeTe-CuTe, as it is observed for the crystalline phases. But there are distinct changes in the short- and intermediate-range order, which can be visualized by comparison with structural results of GeCu<sub>2</sub>Te<sub>3</sub> and GeTe, which our group has already investigated by AXS. The resulting total structure factors are shown in fig. 1. Apparently, all total S(Q) functions show large similarities, only the second main peak around 3.2 Å<sup>-1</sup> is steadily increasing in intensity an shifting towards lower Q values as a function of the CuTe content. Furthermore, the low-Q signal exhibits an increasing trend. Both characteristics are crucial to understand the structure-property relationships in the GCT system.

The in-depth analysis of the intermediate-range order is still ongoing, but even this preliminary analysis shows the importance of determining the content-dependence of structural features to clarify the structureproperty relations. Thus, further experiments are planned to study the GCT system, with special regard to Ge<sub>4</sub>Cu<sub>1</sub>Te<sub>5</sub> (containing 20 atom% CuTe), as it exhibits the highest temperature of crystallization in the entire GeTe-CuTe system, but shows a phase-change density change and optical contrast comparable to GeTe. [1,2]



## References

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- [3] B. Huang and J. Robertson, Phys. Rev. B 81, 081204(R) (2010).